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查询"MT3S45T" 供应商 BA TRANSISTOR SILICON NPN EPITAXIAL PLANER TYPE

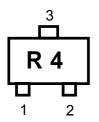
MT3S45T

VCO OSCILLETOR STAGE UHF LOW NOISE AMPLIFIER APPLICATION

FEATURES

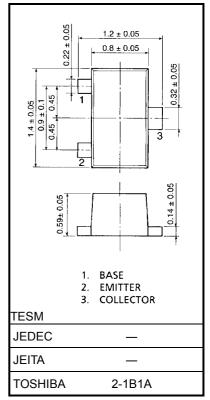
- Low Noise Figure :NF=1.1dB (@f=2GHz)
- High Gain:|S21e|²=12.0dB (@f=2GHz)

Marking



Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit |
|-----------------------------|------------------|---------|------|
| Collector-Base voltage | V _{CBO} | 8 | V |
| Collector-Emitter voltage | V _{CEO} | 4.5 | V |
| Emitter-Base voltage | V _{EBO} | 1.5 | V |
| Collector-Current | Ι _C | 30 | mA |
| Base-Current | Ι _Β | 15 | mA |
| Collector Power dissipation | P _C | 100 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature Range | T _{stg} | -55~150 | °C |



Weight:0.0022g (typ.)

Unit: mm

MicroWave4Chatacteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|----------------------|------------------------|---|------|------|-----|------|
| Transition Frequency | fT | V _{CE} =3V, I _C =20mA, f=2GHz | 13.5 | 18 | - | GHz |
| Insertion Gain | S21e ² (1) | V _{CE} =3V, I _C =20mA, f=1GHz | - | 17.5 | - | dB |
| | S21e ² (2) | V _{CE} =3V, I _C =20mA, f=2GHz | 9.5 | 12 | - | dB |
| Noise Figure | NF(1) | V _{CE} =3V, I _C =6mA, f=1GHz | - | 0.9 | - | dB |
| | NF(2) | V _{CE} =3V, I _C =6mA, f=2GHz | - | 1.1 | 1.6 | dB |

Electrical Characteristics (Ta = 25°C)

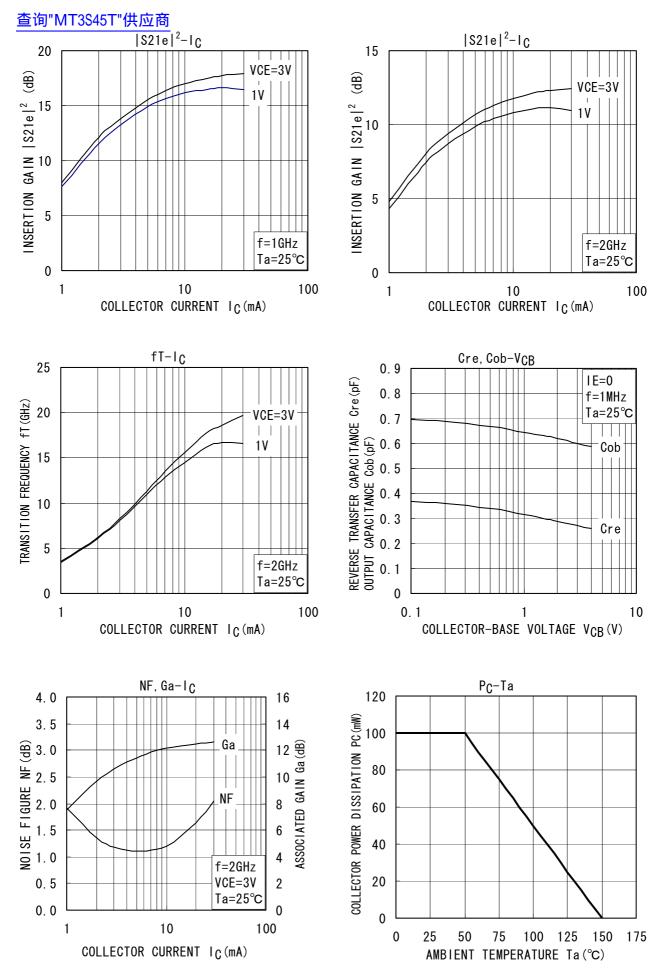
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|---|-----|------|------|------|
| Collector Cut-off Current | I _{CBO} | V _{CB} =8V, I _E =0 | - | - | 1 | μA |
| Emitter Cut-off Current | I _{EBO} | V _{EB} =1V, I _C =0 | - | - | 1 | μA |
| DC Current Gain | hFE | V _{CE} =3V, I _C =10mA | 70 | - | 140 | - |
| Output Capacitance | C _{ob} | V _{CB} =1V, I _E =0, f=1MHz | - | 0.66 | 1.10 | pF |
| Reverse Transistor Capacitance | C _{re} | V _{CB} =1V, I _E =0, f=1MHz (Note 1) | - | 0.33 | 0.55 | pF |

Note 1: Cre is measured by 3 terminal method with capacitance bridge.

Caution: This device is sensitive to electrostatic discharge.

Please make enough tool and equipment earthed when you handle.

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